

First-principles investigation of paramagnetic centers in v-SiO₂, Ge-doped SiO₂ and v-GeO₂.

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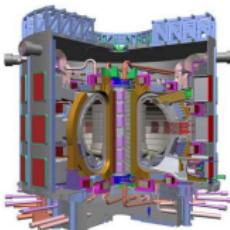
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Motivation: Developing radiation tolerant optical fibers

- ITER plasma diagnostic system



- Space applications



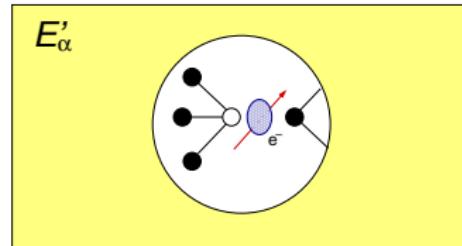
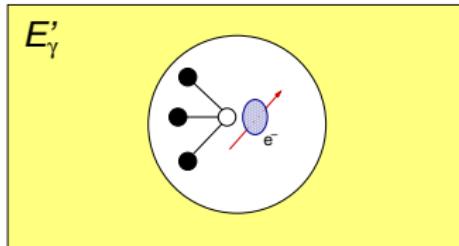
- monitoring systems for nuclear power plants and waste storage



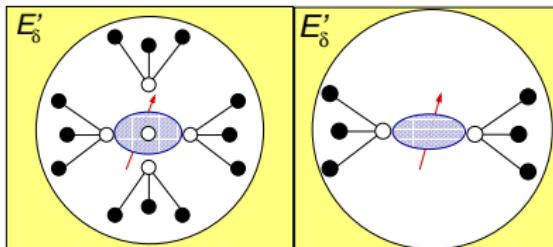
S. Girard et al, IEEE Trans Nucl. Sci. **60**, 2015 (2013).

E' centers in $a\text{-SiO}_2$: E'_γ , E'_α , and E'_δ

Proposed models:



?



?

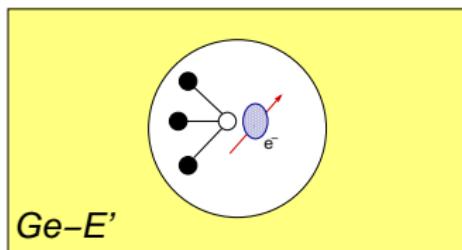
Griscom, Nucl. Inst. & Methods B**1**, 481 (1984).

Buscarino et al. Phys. Rev. Lett **97**, 135502 (2006).

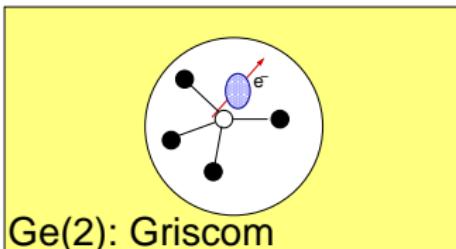
Jivanescu et al. Phys. Rev. B **83**, 094118 (2011).

Ge paramagnetic centers in ν -SiO₂: Ge- E' , Ge(2)

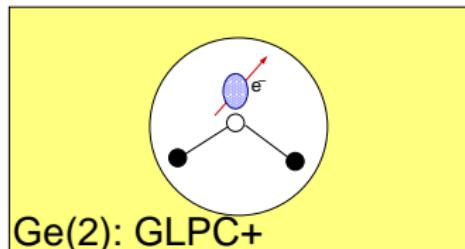
Proposed models:



Ge- E'



Ge(2): Griscom



Ge(2): GLPC+

?

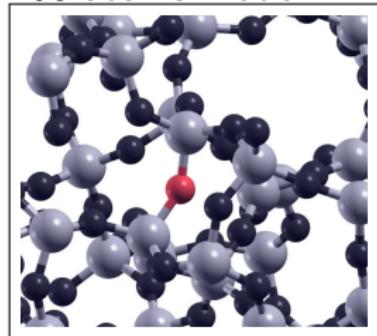
Griscom, Opt. Mater. Express **1**, 400 (2011).

Fujimaki et al. Phys. Rev. B **57**, 3920 (1998).

- GGA exchange-correlation functionals (80 ryd cutoff)
- QE and QE-GIPAW (from www.qe-forge.org/):
g-tensor GIPAW, Pickard and Mauri, PRL **88**, 086403 (2002).

Positively charged oxygen vacancies in $a\text{-SiO}_2$:

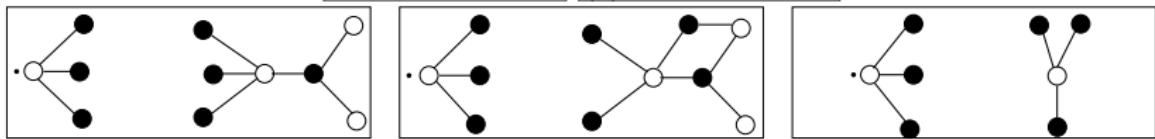
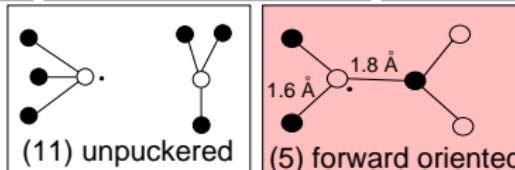
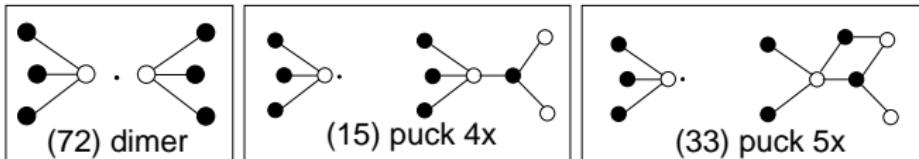
108 atoms model:



- remove a bridging oxygen from a chosen site and relax in the $q = +1$ charged state.
- 72 SiODC models are obtained (Si₂ dimers)
- relax in the $q = +2$ and again in the $q = +1$ (non-dimers)

EPR parameters of E' centers: configurations

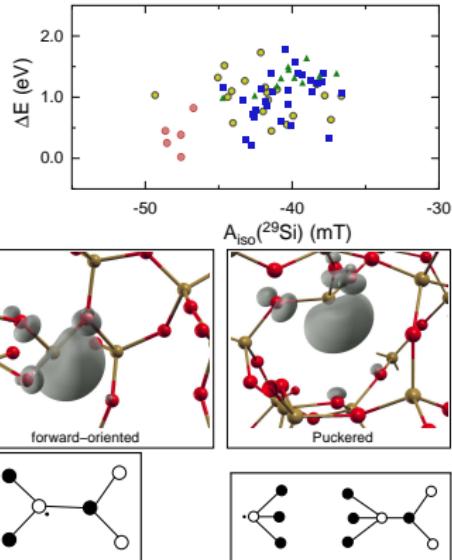
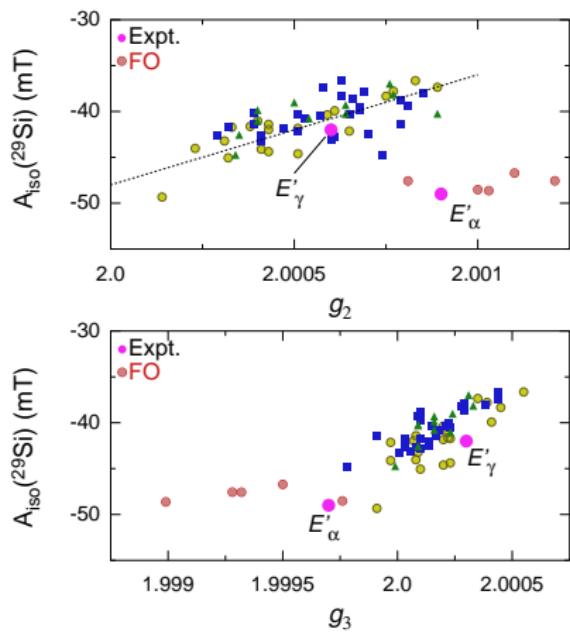
Configurations obtained after ab initio relaxation of SiODC models:



L. Giacomazzi, L. Martin-Samos, A. Boukenter, Y. Ouerdane, S. Girard, N. Richard, PRB 90, 014108 (2014).

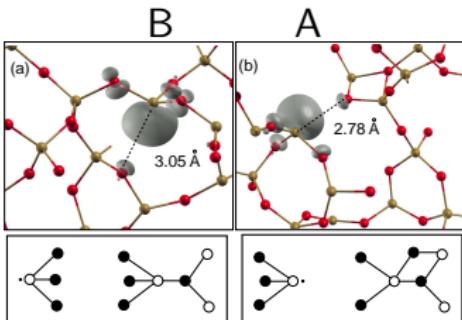
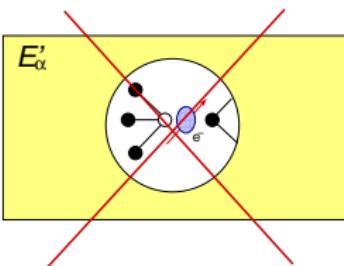
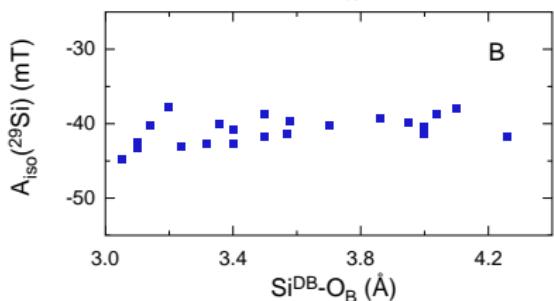
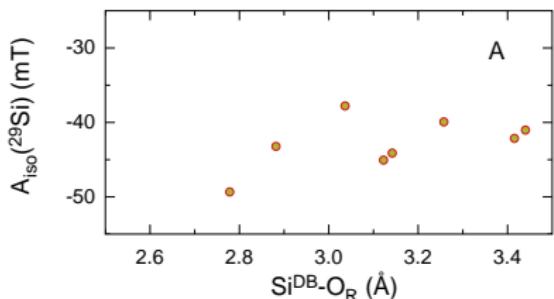
Uchino et al PRB 74, 125203 (2006); PRL 84, 1475 (2000).

Results: Si DB puckered, unpuckered, and forward-oriented (FO) configurations



No way to find puckered configurations with $A \sim -49$ mT and $g_2 \sim 2.0010$ as shown by the E'_α .

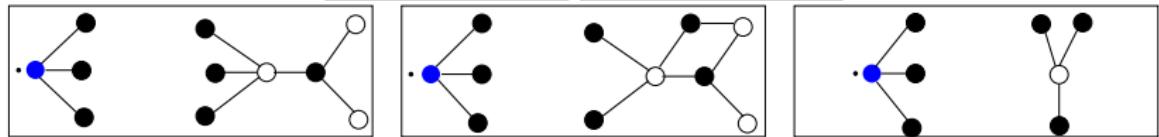
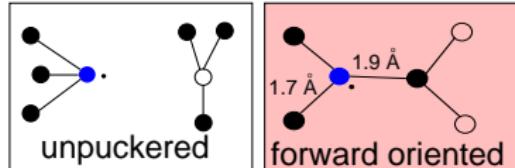
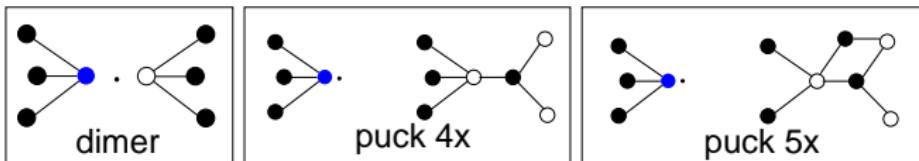
Si DB "interacting" model of the E'_α ?



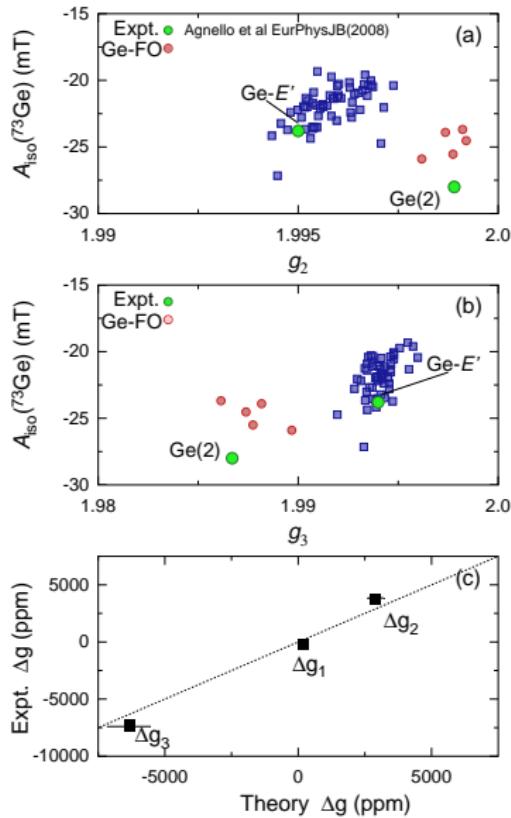
- trends could exist but local environment strongly affect $A_{\text{iso}}(\text{Si})$
- distance $\text{Si}^{\text{DB}}-\text{O}^{\text{B},\text{R}} \sim 3 \text{ \AA}$ does not seem a criterion supporting the existence of an E' center at 49 mT.

EPR parameters of Ge centers: configurations

Configurations obtained after ab initio relaxation of GeODC models:



EPR parameters of Ge- E' and Ge-FO: distributions



- Ge puckered \rightarrow Ge- E'
- Ge-FO \rightarrow Ge(2)

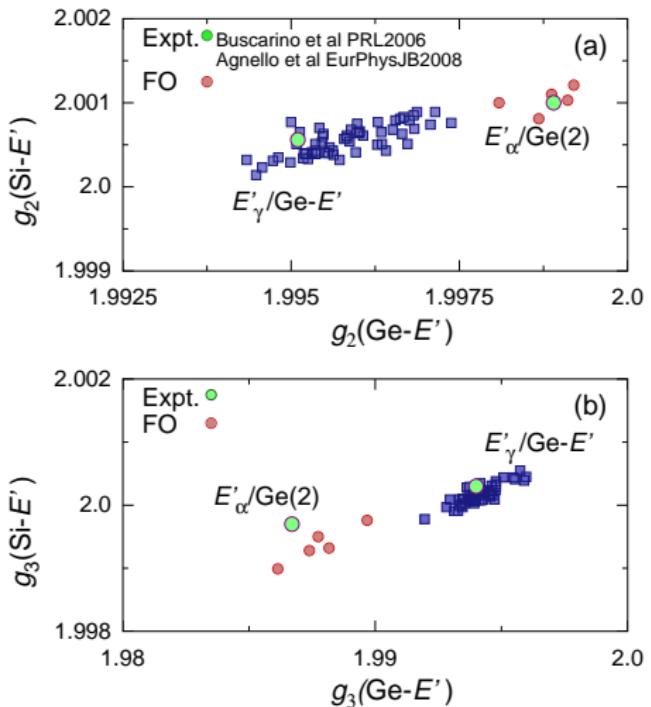
Expt.:

$$\Delta g_i = g_i(\text{Ge}(2)) - g_i(\text{Ge} - \text{E}')$$

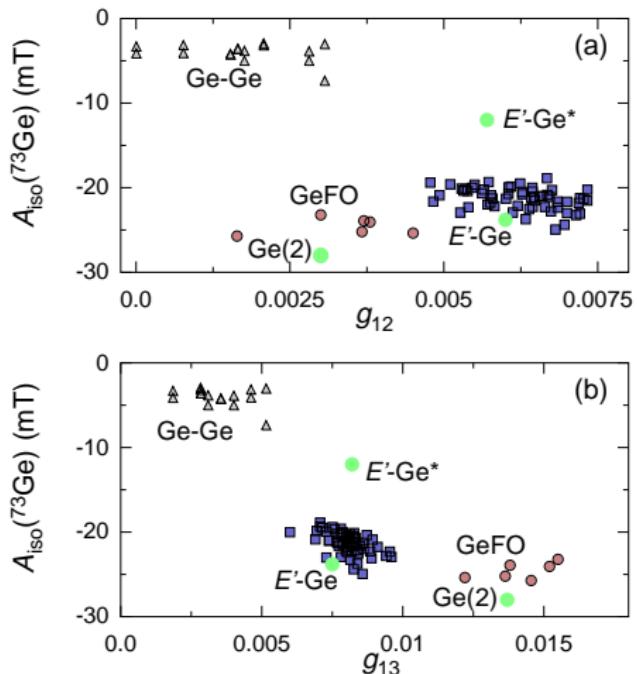
Theory:

$$\Delta g_i = g_i(\text{GeFO}) - g_i(\text{Ge} - \text{E}'_c)$$

Ge(2) i.e. the Ge analogue of the E'_α

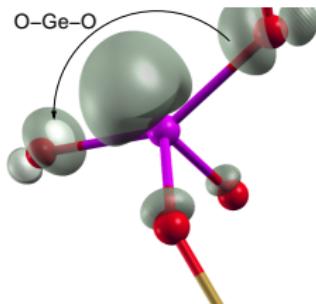
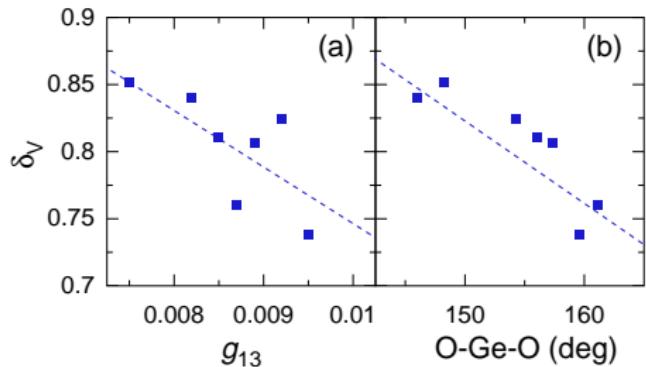


The Ge(2) center in pure ν -GeO₂



Giacomazzi, Martin-Samos, Richard, Microel Eng. **147**, 130 (2015).

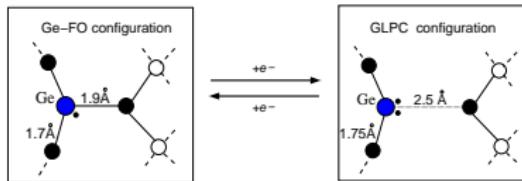
The Ge(2) is not a trapped elect. center as Ge(1)!



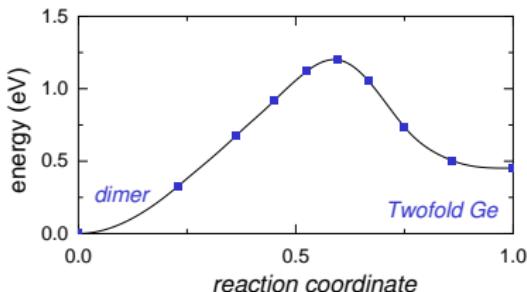
In Ge(2) $g_{13} = 0.0140$: for Griscom's model to be true it implies a highly deformed GeO_4^- tetrahedron with $\delta_Y \sim 0.5$ as for O-Ge-O $\sim 180^\circ$.

L. Giacomazzi *et al.* Opt. Mater. Express **5**, 1054 (2015).

Twofold Si and Ge (GLPC): *in progress*

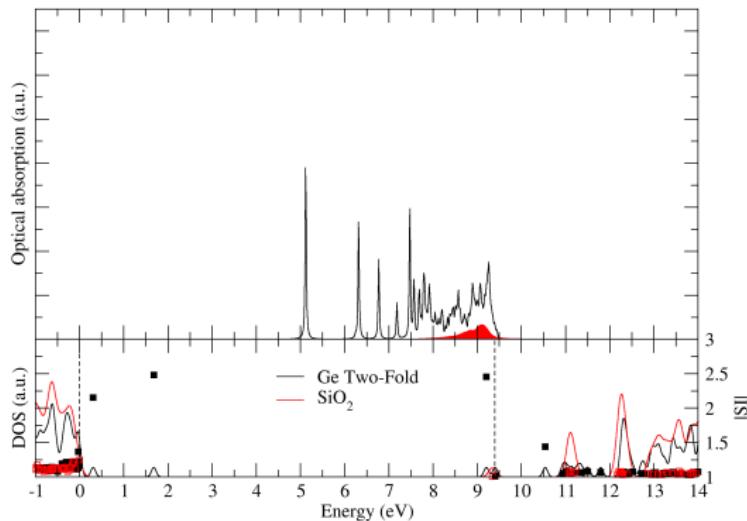


By first principles relaxation of the neutral Ge-FO a two-fold Ge is obtained. This is consistent with the observed Ge(2) generation from GLPC [Agnello et al Eur. Phys. J. B 61, 25 (2008)].



A neutral Ge-Si (Si-Si) dimer can transform into a twofold Ge (Si) configuration by overcoming ~ 1 eV (~ 2) barrier.

Twofold Si and Ge (GLPC): *in progress*



Just in case you doubt it is really a GeODC(II): calculations of the optical absorption spectrum gives a peak at 5.1 eV !
Giacomazzi, Martin-Samos, Richard et al *in progress* (2015).

Conclusions

- E'_α arises from "forward-oriented" configurations, while no clear evidence is found for the Si DB "interacting model".
- Ge(2) originates from Ge-FO and thus is the Ge analogue of the E'_α center.
- As shown by this work, first-principles calculations of EPR parameters are a powerful tool for studying paramagnetic defects, not only for E' centers in vitreous silica but also in doped silica (e.g. Ge(2) and Ge- E' in Ge-doped SiO_2).
- Calculations of the optical absorption spectra are in progress for the twofold Si and Ge configurations derived from the Si-FO and Ge-FO.

L. Giacomazzi, L. Martin-Samos, A. Boukenter, Y. Ouerdane, S. Girard, N. Richard, Opt. Mater Express **5**, 1054 (2015).

L. Giacomazzi, Martin-Samos, N. Richard, Microel. Eng. **147**, 130 (2015).

L. Giacomazzi *et al* Phys. Rev. B **90**, 014108 (2014).

Thank you for your attention